



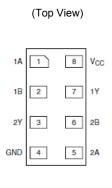
Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G08 is a dual two input AND gate. Both gates have push-pull outputs designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down. Each gate performs the positive Boolean function:

$$Y = A \cdot B$$
 or $Y = \overline{\overline{A} + \overline{B}}$

Pin Assignments



X2-DFN1210-8

Applications

- Suited for Battery and Low Power Needs
 - Wide Array of Products Such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation/GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption I_{CC} < 0.9µA
- Low Dynamic Power Consumption
 C_{PD} = 6 pF (Typical at 3.6V)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at $V_{CC} = 3.0V$
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114) Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

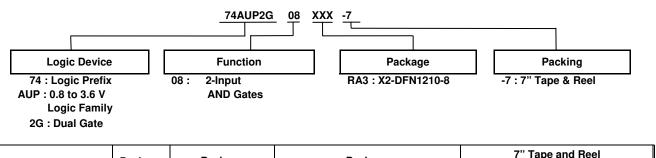
Notes:

 No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



	Package	Package	Package		u neer
Device	Code	(Notes 4 & 5)	Size	Quantity Part N Su	
74AUP2G08RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

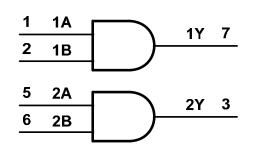
5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

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Pin Name	Pin	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram



Function Table

Inp	Inputs						
Α	В	Y					
L	L	L					
L	Н	L					
Н	L	L					
Н	Н	Н					



Absolute Maximum Ratings (Note 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	50	mA
I _{ОК}	Output Clamp Current ($V_0 < 0$)	50	mA
lo	Continuous Output Current ($V_O = 0$ to V_{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	P	arameter	Min	Max	Unit
V _{CC}	Operating Voltage	—	0.8	3.6	V
VI	Input Voltage	•	0	3.6	V
Vo	Output Voltage		0	Vcc	V
		$V_{CC} = 0.8V$	—	-20	μA
		V _{CC} = 1.1V	—	-1.1	
	Lligh Lough Output Current	V _{CC} = 1.4V	—	-1.7	
I _{ОН}		V _{CC} = 1.65V	—	-1.9	mA
		V _{CC} = 2.3V	—	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
		V _{CC} = 1.4V	_	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	—	3.1	1
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	—	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics

Symbol	Parameter	Test Conditions	V	T _A = -	+25°C	T _A = -40°C	C to +85°C	Unit
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	—	
N	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	—	v
VIH	Voltage	_	2.3V to 2.7V	1.6	_	1.6	—	v
		-	3.0V to 3.6V	2.0	—	2.0	—	
		1	0.8V to 1.65V	_	$0.30 \times V_{CC}$	—	$0.30 \times V_{CC}$	
VIL	Low-Level Input	1	1.65V to 1.95V	_	$0.35 \times V_{CC}$	—	0.35 X V_{CC}	v
VIL	Voltage	-	2.3V to 2.7V	—	0.7	—	0.7	v
		_	3.0V to 3.6V	_	0.9	—	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	$V_{CC} - 0.1$	—	$V_{CC} - 0.1$	—	
		I _{OH} = -1.1mA	1.1V	0.75 X V_{CC}	—	0.7 X V _{CC}	—	
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—	
	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	—	1.3	—	.,
V _{OH}	Voltage	I _{OH} = -2.3mA	2.21/	2.05		1.97	—	V
		I _{OH} = -3.1mA	- 2.3V	1.9	_	1.85	—	
		I _{OH} = -2.7mA	0)/	2.72	_	2.67	—	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μΑ	0.8V to 3.6V		0.1		0.1	
	Ì	I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	—	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
.,	Low-Level Input	I _{OL} = 1.9mA	1.65V		0.31		0.35	
V _{OL}	Voltage	I _{OL} = 2.3mA	0.01/		0.31		0.33	V
		I _{OL} = 3.1mA	- 2.3V		0.44		0.45	
		I _{OL} = 2.7mA	<i></i>	_	0.31	_	0.33	
		I _{OL} = 4mA	- 3V		0.44	—	0.45	
lı	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 0V \text{ to } 3.6V$	0V	—	± 0.2	—	± 0.6	μA
ΔI_{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0V to 0.2V	—	± 0.2	—	± 0.6	μA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	0.5	—	0.9	μA
ΔI _{CC}	Additional Supply Current	One Input at V_{CC} –0.6V Other Inputs at V_{CC} or GND	3.3V	—	40	—	50	μA



Electrical Characteristics (cont.)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Unit
V _{IL} Lo V _{OH} Hi V _{OL} Lo		—	0.8V to 1.65V	0.80 X V _{CC}	—	
Maria	High-Level Input Voltage		1.65V to 1.95V	0.70 X V _{CC}	—	V
VIH			2.3V to 2.7V	1.6	—	v
			3.0V to 3.6V	2.0		
			0.8V to 1.65V		0.25 X V_{CC}	
Vu	Low-Level Input Voltage	_	1.65V to 1.95V		$0.30 \times V_{CC}$	V
۷IL			2.3V to 2.7V		0.7	v
			3.0V to 3.6V	_	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11	_	
		I _{OH} = -1.1mA	1.1V	$0.6 \times V_{CC}$	—	
		I _{OH} = -1.7mA	1.4V	0.93	_	
Vон		I _{OH} = -1.9mA	1.65V	1.17	—	V
VOH	High-Level Output Voltage	I _{OH} = -2.3mA	0.01/	1.77	—	V
		I _{OH} = -3.1mA	2.3V	1.67	—	
		I _{OH} = -2.7mA	2)/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
.,		I _{OL} = 1.9mA	1.65V	_	0.39	
VOL	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA	a) (_	0.36	
		I _{OL} = 4mA	3V		0.50	
h	Input Current	A or B Input, V _I = GND to 3.6V	0V to 3.6V	_	± 0.75	μA
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	3.0	μA
ΔI _{CC}	Additional Supply Current	Input at V_{CC} –0.6V Other Inputs at V_{CC} or GND	3.3V	_	75	μA

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Tes Condit		V _{CC}	Тур	Unit	
				0.8V	5.1		
				1.2V ± 0.1V	5.2		
0	Power Dissipation	f = 1N	ЛНz	1.5V ± 0.1V	5.2	1	
C _{pd}	Capacitance	No Lo	oad	1.8V ± 0.15V	5.5	pF	
				2.5V ± 0.2V	5.7		
				3.3V ± 0.3V	6.0		
Ci	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF	
θ」Α	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	—	+395	°C/W	
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	+236	°C/W	

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From	To Output	Vcc	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input			Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	19.6	—	—	_	_	—	
	A or B		1.2V ± 0.1V	2.6	5.1	11.9	2.1	12.9	2.1	14.2	- ns
		Y	1.5V ± 0.1V	1.6	3.7	6.5	1.5	7.5	1.5	8.3	
t _{pd}			1.8V ± 0.15V	1.3	3.0	5.2	1.3	6.1	1.3	6.7	
			2.5V ± 0.2V	1.1	2.4	4.0	1.0	4.8	1.0	5.3	
			3.3V ± 0.3V	1.0	2.2	3.5	0.9	4.3	0.9	4.8	

C_L = 10pF, See Figure 1

Parameter	From	To Output	V _{cc}	T _A = +25°C			T _A = -40°C	C to +85°C	T _A = -40°C	A = -40°C to +125°C	
Farameter	Input			Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	23.7	_	_	—	_	_	
	A or B		1.2V ± 0.1V	2.4	6.0	13.8	2.2	15.0	2.2	16.5	- ns
		v	1.5V ± 0.1V	2.0	4.3	7.6	1.8	8.9	1.8	9.8	
t _{pd}		Ŷ	1.8V ± 0.15V	1.7	3.6	6.1	1.6	7.2	1.6	7.9	
			2.5V ± 0.2V	1.4	2.9	4.8	1.3	5.7	1.3	6.3	
			3.3V ± 0.3V	1.3	2.7	4.2	1.2	4.7	1.2	5.2	

C_L = 15pF, See Figure 1

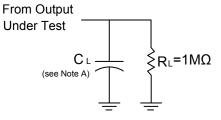
Parameter	From	To Output	V _{cc}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input			Min	Тур	Max	Min	Max	Min	Max	Onit
			0.8V	_	27.7	_	_	_	_	_	
	A or B		1.2V ± 0.1V	3.4	6.8	15.6	3.1	19.3	3.1	19.5	ns
		v	1.5V ± 0.1V	2.3	4.9	8.6	2.1	10.1	2.1	11.2	
t _{pd}			1.8V ± 0.15V	1.9	4.0	6.9	1.8	8.2	1.8	9.0	
			2.5V ± 0.2V	1.7	3.4	5.5	1.6	6.5	1.6	7.2	
			3.3V ± 0.3V	1.4	3.1	4.8	1.4	5.9	1.4	6.5	

C_L = 30pF, See Figure 1

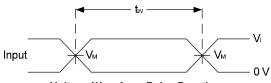
Parameter	From	From To V _{CC}		T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input	Output	VCC	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	39.6	_	_	_	_	_	
	A or B		1.2V ± 0.1V	4.6	9.1	21.3	4.1	26.8	4.1	27.0	- ns
		Y	1.5V ± 0.1V	3.4	6.4	11.5	2.9	13.6	2.9	15.0	
t _{pd}			1.8V ± 0.15V	2.6	5.3	9.1	2.4	10.9	2.4	12.1	
			2.5V ± 0.2V	2.3	4.5	7.2	2.2	8.6	2.2	9.5	
			3.3V ± 0.3V	1.9	4.2	6.2	1.8	7.5	1.8	8.3	



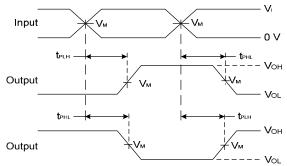
Parameter Measurement Information



Vcc	Inputs		М	0
	VI	t _r /t _f	V _M	C∟
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied a pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.

D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8

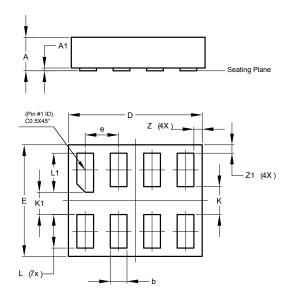


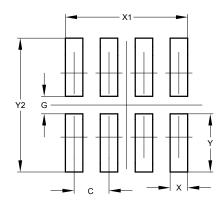
- $\frac{XX}{Y} : \text{ Identification Code}$ $\frac{Y}{Y} : \text{ Year : } 0 \sim 9$ $\frac{W}{Y} : \text{ week : } A \sim Z : 1 \sim 26 \text{ week}$ $a \sim z: 27 52 \text{ week}$ z represents 52 and 53 week
- \underline{X} : week : A~Z : Internal code

Part Number	Package	Identification Code	
74AUP2G08RA3-7	X2-DFN1210-8	СТ	

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
Е	0.95	1.05	1.00	
е	-	-	0.30	
К	-	-	0.25	
K1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z1	0.050	0.100	0.075	
All Dimensions in mm				

Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
¥1	1.150	



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